# Power MOSFET 20V, 125m $\Omega$ , 2A, Single N-Channel

This low-profile high-power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and ultra low on resistance. This device is suitable for applications with low gate charge driving or ultra low on resistance requirements.

#### **Features**

- Low On-Resistance
- 1.8V drive
- ESD Diode-Protected Gate
- Pb-Free, Halogen Free and RoHS compliance
- Ultra small package SCH6 (1.6mm×1.6mm×0.56mmt)

# **Typical Applications**

• Load Switch

#### **SPECIFICATIONS**

#### **ABSOLUTE MAXIMUM RATING** at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	20	V
Gate to Source Voltage	VGSS	±12	V
Drain Current (DC)	ΙD	2	Α
Drain Current (Pulse) PW ≤ 10μs, duty cycle ≤ 1%	IDP	8	Α
Power Dissipation When mounted on ceramic substrate (900mm² × 0.8mm)	PD	0.8	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit		
Junction to Ambient When mounted on ceramic substrate (900mm² × 0.8mm)	$R_{\theta JA}$	156.2	°C/W		

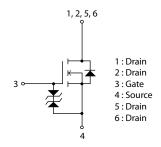


# ON Semiconductor®

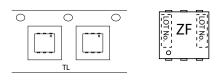
www.onsemi.com

VDSS	R <sub>DS</sub> (on) Max	ID Max
	125mΩ@ 4.5V	
20V	190mΩ@ 2.5V	2A
	310mΩ@ 1.8V	

# ELECTRICAL CONNECTION N-Channel



#### PACKING TYPE : TL MARKING



#### ORDERING INFORMATION

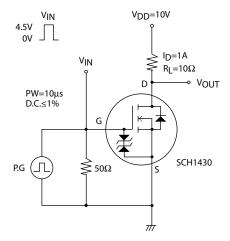
See detailed ordering and shipping information on page 5 of this data sheet.

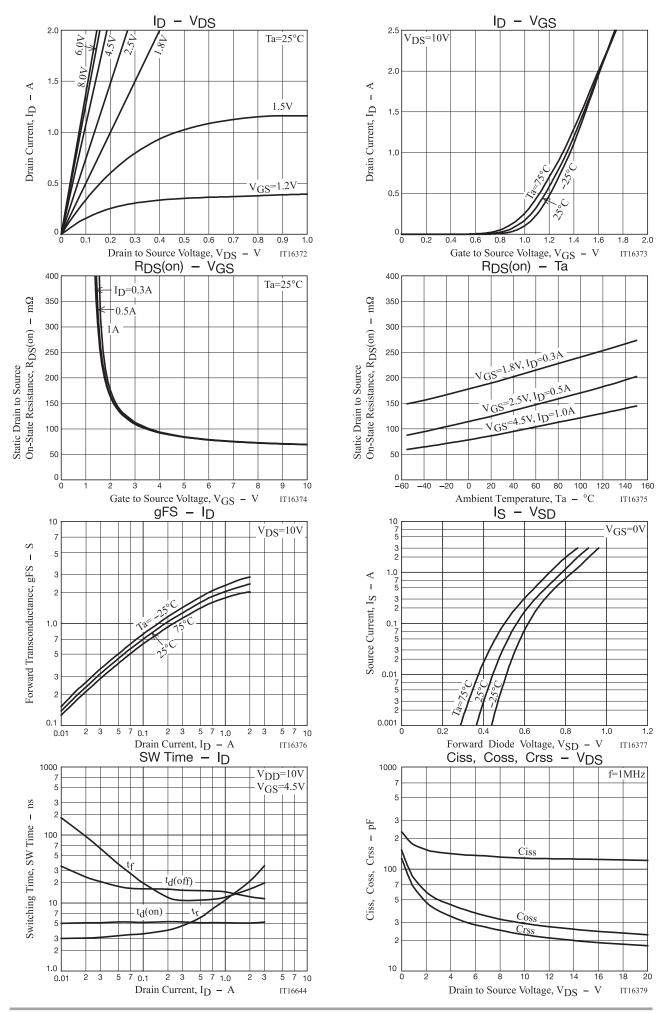
## **ELECTRICAL CHARACTERISTICS** at Ta = 25°C (Note 2)

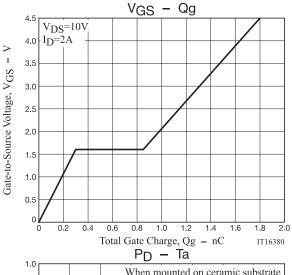
Parameter	Symbol	Conditions	Value			Unit
Farameter	Symbol Conditions		min	typ	max	Offic
Drain to Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			1	μΑ
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μΑ
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	0.4		1.3	V
Forward Transconductance	gFS	V <sub>DS</sub> =10V, I <sub>D</sub> =1A		1.9		S
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =1A, V <sub>GS</sub> =4.5V		93	125	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =0.5A, V <sub>GS</sub> =2.5V		135	190	mΩ
	R <sub>DS</sub> (on)3	I <sub>D</sub> =0.3A, V <sub>GS</sub> =1.8V		200	310	mΩ
Input Capacitance	Ciss			128		pF
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		28		pF
Reverse Transfer Capacitance	Crss			21		pF
Turn-ON Delay Time	t <sub>d</sub> (on)			5.1		ns
Rise Time	tr	Con an arified Took Circuit		11		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit		14.5		ns
Fall Time	tf			12		ns
Total Gate Charge	Qg			1.8		nC
Gate to Source Charge	Qgs	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =2A		0.3		nC
Gate to Drain "Miller" Charge	Qgd			0.55		nC
Forward Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> =2A, V <sub>GS</sub> =0V		0.85	1.2	V

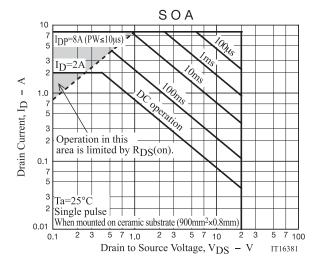
Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

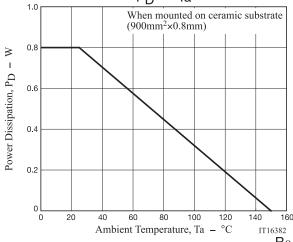
# **Switching Time Test Circuit**

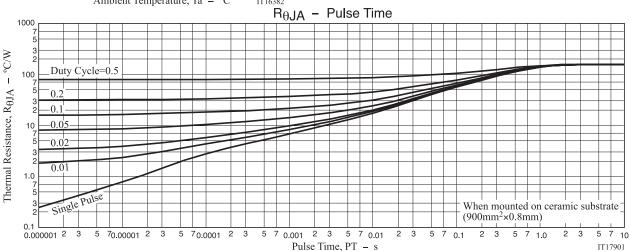






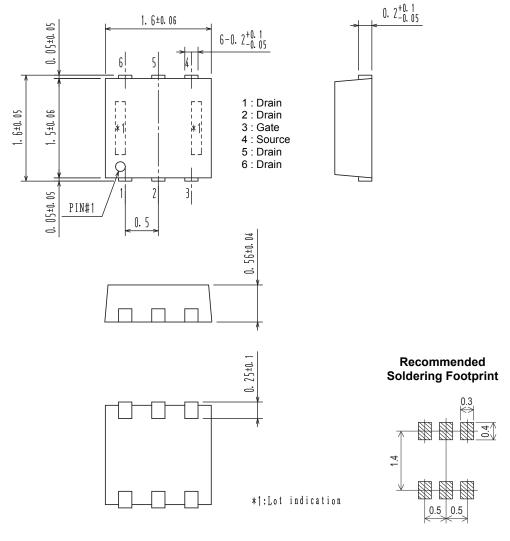






#### PACKAGE DIMENSIONS

unit: mm SOT-563 / SCH6 CASE 463AB ISSUE O



#### ORDERING INFORMATION

ONDERING IN ORMATION					
Device	Marking	Package	Shipping (Qty / Packing)		
SCH1430-TL-H	75	SOT-563 / SCH6	5 000 / Tone 9 Deal		
SCH1430-TL-W	ZF	(Pb-Free / Halogen Free)	5,000 / Tape & Reel		

<sup>†</sup> For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub\_link/Collateral/BRD8011-D.PDF

Note on usage: Since the SCH1430 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

ON Semiconductor and the ON logo are registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent re